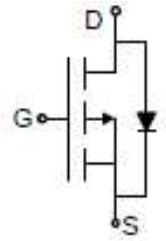
P-Channel Power MOSFET

Features

- V_{DS}=-20V, I_D=-50A
  $R_{DS(ON)}$<8.5mΩ @ V_{GS} = -4.5V
  $R_{DS(ON)}$ <12mΩ @ V_{GS} = -2.5V
- High Power and Current Handing Capability
- Lead Free Product is Acquired
- Surface Mount Package

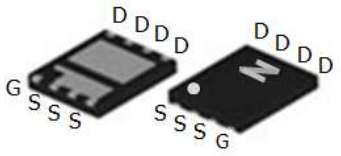


Schematic Diagram

Application

- PWM Applications
- Load Switch

Package



DFN3 x 3

Absolute Maximum Ratings (T_C=25℃ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		-20	V
V_{GSS}	Gate-Source Voltage		±12	V
I_D	Continuous Drain Current	T_C = 25℃	-50	A
		T_C = 100℃	-32	
I_{DM}	Pulsed Drain Current note1		-200	A
P_D	Power Dissipation	T_C= 25℃	40	W
$R_{\theta JC}$	Thermal Resistance, Junction to Ambient		3.0	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +175	℃

Electrical Characteristics (T_C=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D= -250μA	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = -20V, V_{GS} = 0V,	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= -250μA	-0.35	-0.65	-1.0	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note2	V_{GS} =-4.5V, I_D =-15A	-	6.6	8.5	mΩ
		V_{GS} =-2.5V, I_D =-12A	-	8	12	
g_{FS}	Forward Transconductance	V_{DS} =-5V, I_D = -10A	-	36	-	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} =-10V, V_{GS} =0V, f = 1.0MHz	-	4590	-	pF
C_{oss}	Output Capacitance		-	505	-	pF
C_{rss}	Reverse Transfer Capacitance		-	440	-	pF
Q_g	Total Gate Charge	V_{DS} =-10V, I_D =-15A, V_{GS} =-4.5V	-	46	-	nC
Q_{gs}	Gate-Source Charge		-	7.3	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	10	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD} =-10V, I_D =-14A, R_{GEN}=2.7Ω, V_{GS} =-10V	-	8	-	ns
t_r	Turn-on Rise Time		-	59	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	111	-	ns
t_f	Turn-off Fall Time		-	43	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-50	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-200	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S =-20A	-	-	-1.2	V
trr	Reverse Recovery Time	T_j=25℃,I_{SD}=-15A, V_{GS}=0V di/dt=-100A/μs	-	18	-	ns
Qrr	Reverse Recovery Charge		-	7.7	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

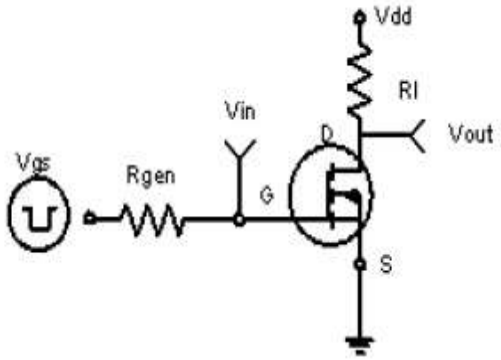


Figure1 :Switching Test Circuit

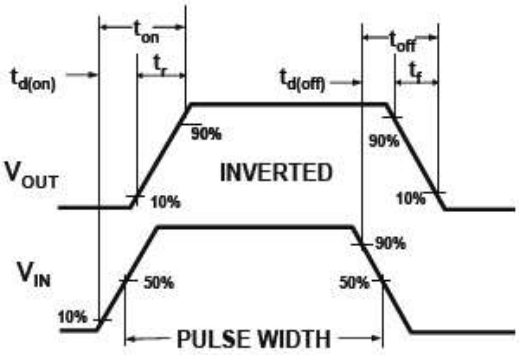
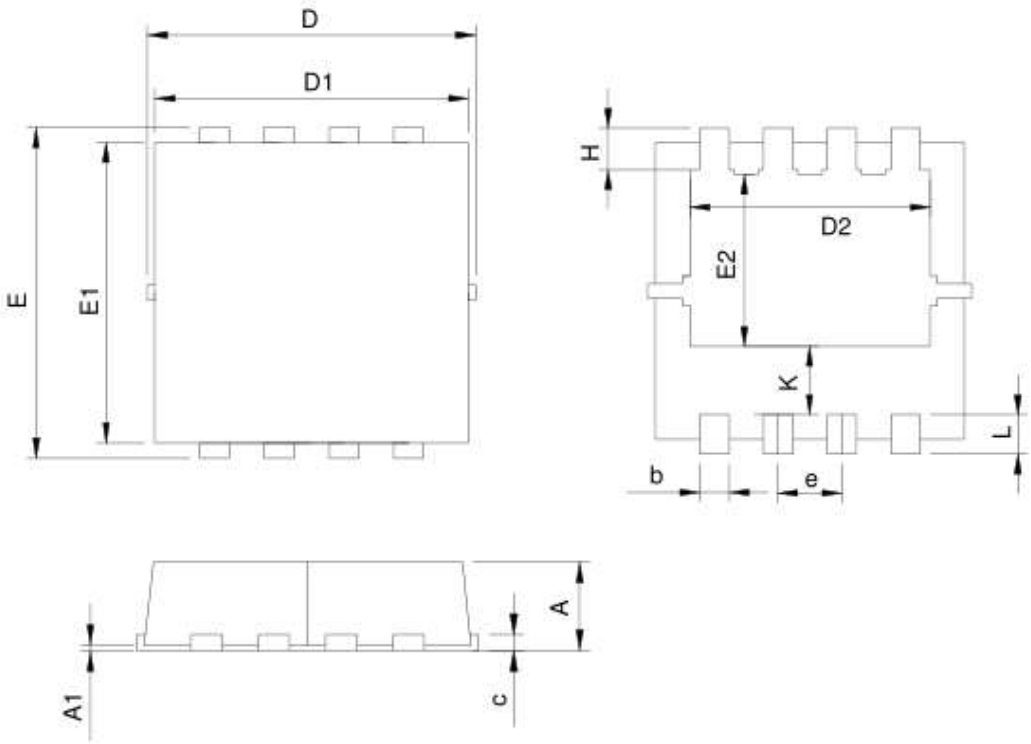


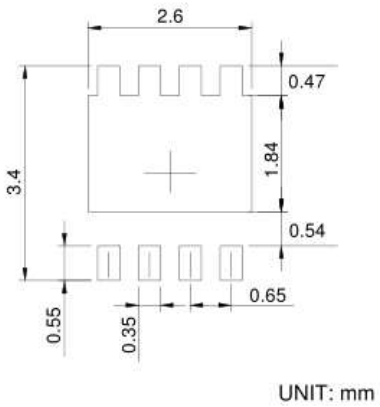
Figure2:Switching Waveforms

●**Dimensions(DFN3×3)**



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET ***category:***

Click to view products by Quan Li ***manufacturer:***

Other Similar products are found below :

614233C 648584F MCH3443-TL-E MCH6422-TL-E NTNS3A92PZT5G IRFD120 IRFF430 JANTX2N5237 2N7000 AOD464 2SK2267(Q) 2SK2545(Q,T) 405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C IPS70R2K0CEAKMA1 BSF024N03LT3 G PSMN4R2-30MLD TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 NTE2969 NTE6400A DMC2700UDMQ-7 DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 IRF40H233XTMA1 IPSA70R950CEAKMA1 IPSA70R2K0CEAKMA1 STU5N65M6 C3M0021120D DMN6022SSD-13